



# CHENMKO ENTERPRISE CO.,LTD

## SURFACE MOUNT EPITAXIAL Transistor

VOLTAGE 20 Volts CURRENT 700 mAmpere

**CHT8050PT**

Lead free devices

### FEATURE

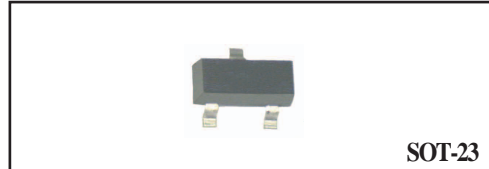
- \* Small surface mounting type. (SOT-23)
- \* High DC current .

### CONSTRUCTION

- \* NPN transistors in one package.

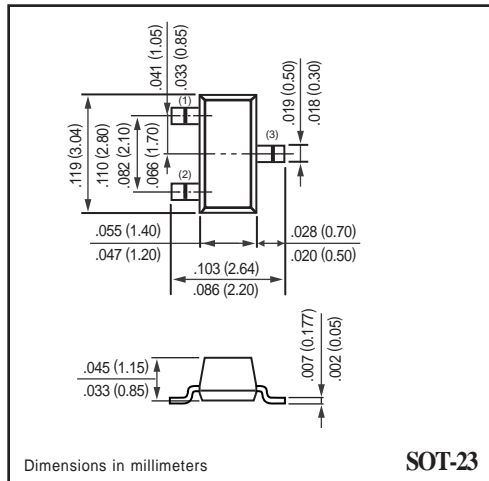
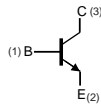
### MARKING

- \* D805
- \* E805



**SOT-23**

### CIRCUIT



### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	-	25	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	20	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	5	V
I <sub>C</sub>	collector current (DC)		-	700	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	-	225	mW
T <sub>stg</sub>	storage temperature		-55	+150	°C
T <sub>j</sub>	junction temperature		-	150	°C
T <sub>amb</sub>	operating ambient temperature		-55	+150	°C

### Note

1. Transistor mounted on an FR4 printed-circuit board.

2008-01

## RATING CHARACTERISTIC CURVES ( CHT8050PT )

### CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{(BR)CBO}$	collector-base breakdown voltage	$I_C = -10\mu\text{A}$ ; $I_E = 0\text{A}$	25	–	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	$I_C = -1\text{mA}$ ; $I_B = 0\text{A}$	20	–	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	$I_E = -10\mu\text{A}$ ; $I_C = 0\text{A}$	5	–	V
$I_{CBO}$	collector cut-off current	$V_{CB} = 20\text{V}$	–	1.0	$\mu\text{A}$
$I_{EBO}$	emitter cut-off current	$V_{EB} = 5\text{V}$	–	100	nA
$h_{FE}$	DC current gain	$I_C = 150\text{ mA}$ ; $V_{CE} = 1\text{V}$	150	500	
$V_{CEsat}$	collector-emitter saturation	$I_C = 500\text{ mA}$ ; $I_B = 50\text{ mA}$	–	500	mV
$V_{BEon}$	base-emitter voltage	$I_C = 150\text{ mA}$ ; $V_{CE} = 1.0\text{V}$	–	1000	mV
$C_{cb}$	output capacitance	$V_{CB} = -10\text{V}$ ; $f = 1.0\text{MHz}$ ; $I_E = 0$	–	10	pF
$f_T$	transition frequency	$V_{CB} = 10\text{V}$ ; $I_C = 20\text{mA}$ ; $f = 100\text{MHz}$	150	–	MHz

2.  $h_{FE}$ : D Classification: 150–300  
 E Classification: 250–500

## RATING CHARACTERISTIC CURVES ( CHT8050PT )

Figure 1. Collector-Emitter Saturation Voltage vs Collector Current

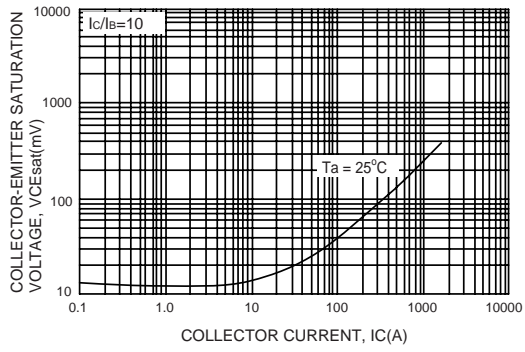


Figure 2. Base-Emitter Saturation Voltage vs Collector Current

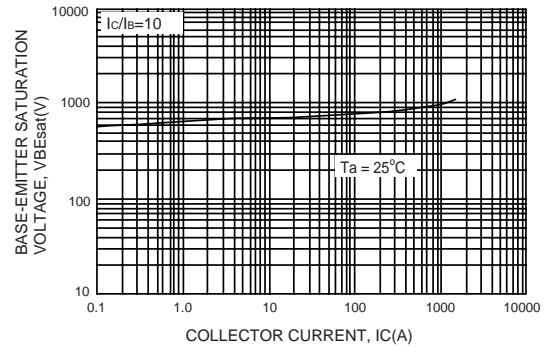


Figure 3. DC Current Gain

